

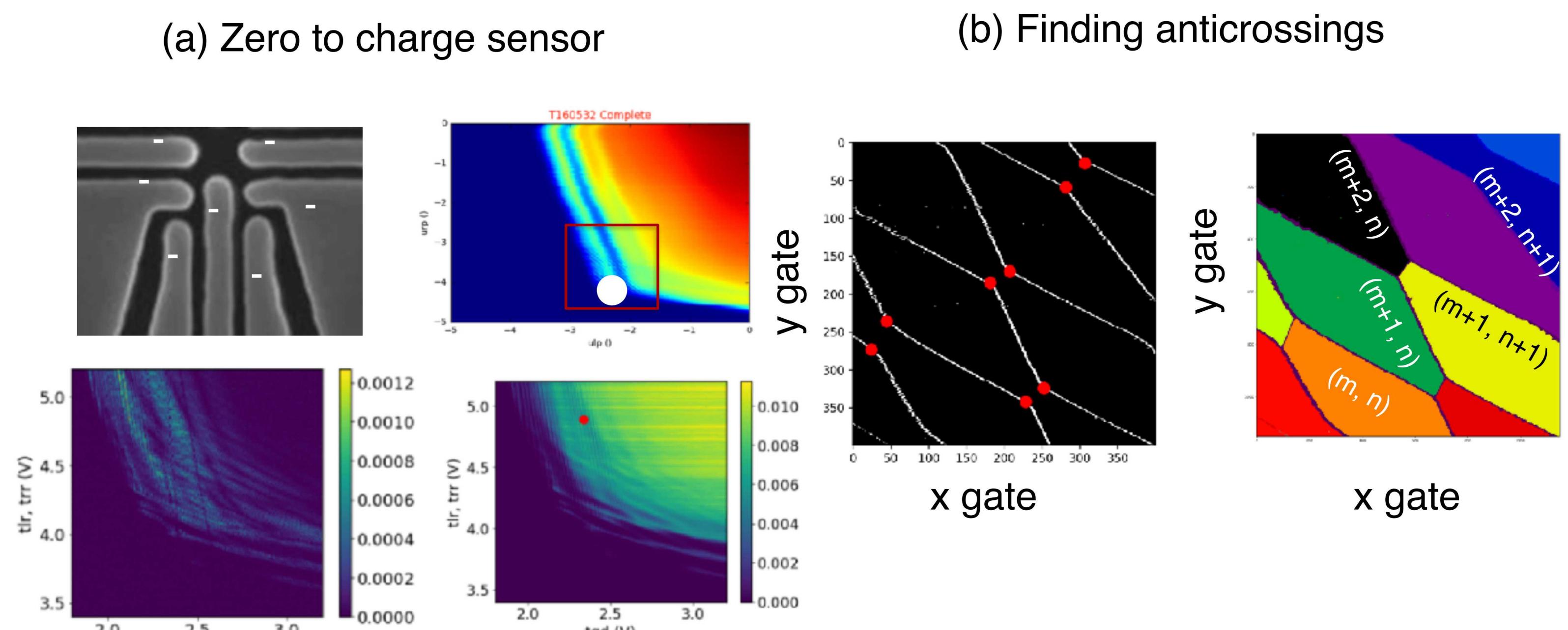
Feature detection and automation in Si MOS quantum dots toward automated qubit tuning

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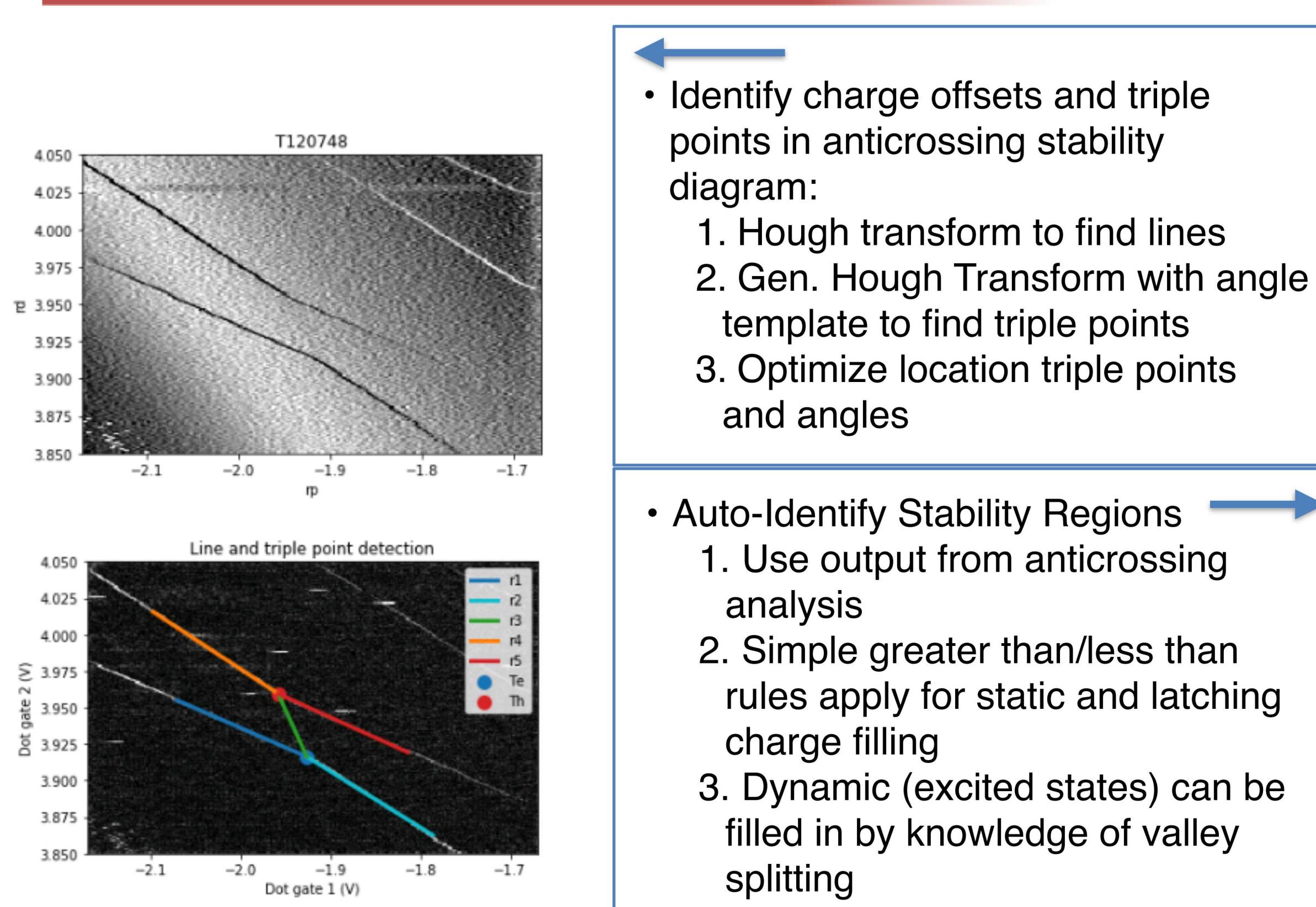
Introduction

- Challenging tuning conditions and complex devices lead to a need for automated measurements and analysis [1]
- A few groups have shown some automation steps and automated analysis.[2, 3, 4, 5, 6]
- Previously we've shown that
 - Auto tune from no voltages to working charge sensor
 - Detect multiple charge offsets and anticrossings in a large voltage space
- Here we show a feed forward automation protocol starting at an anticrossing to generating pulse sequences toward qubit calibration

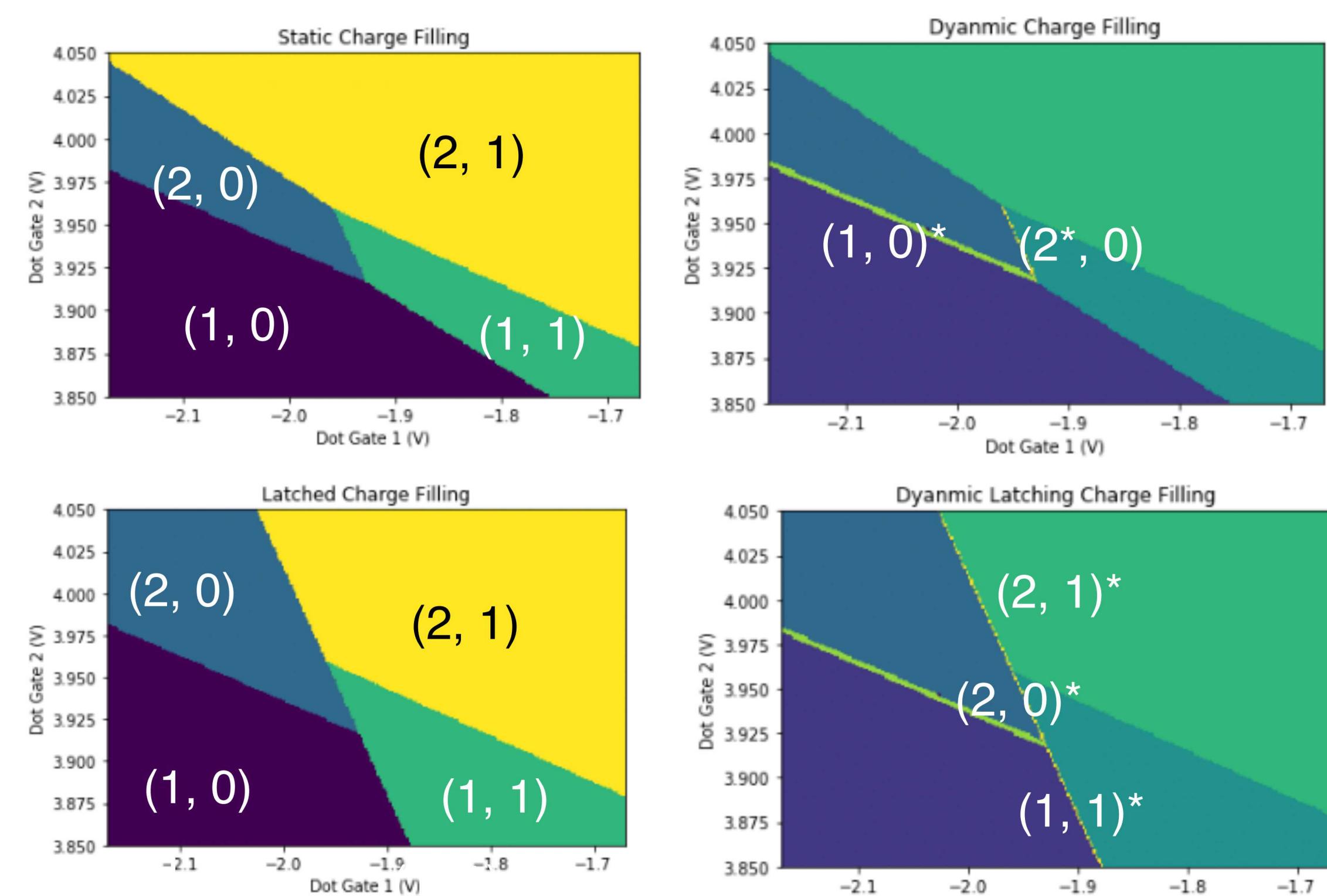
Previous work



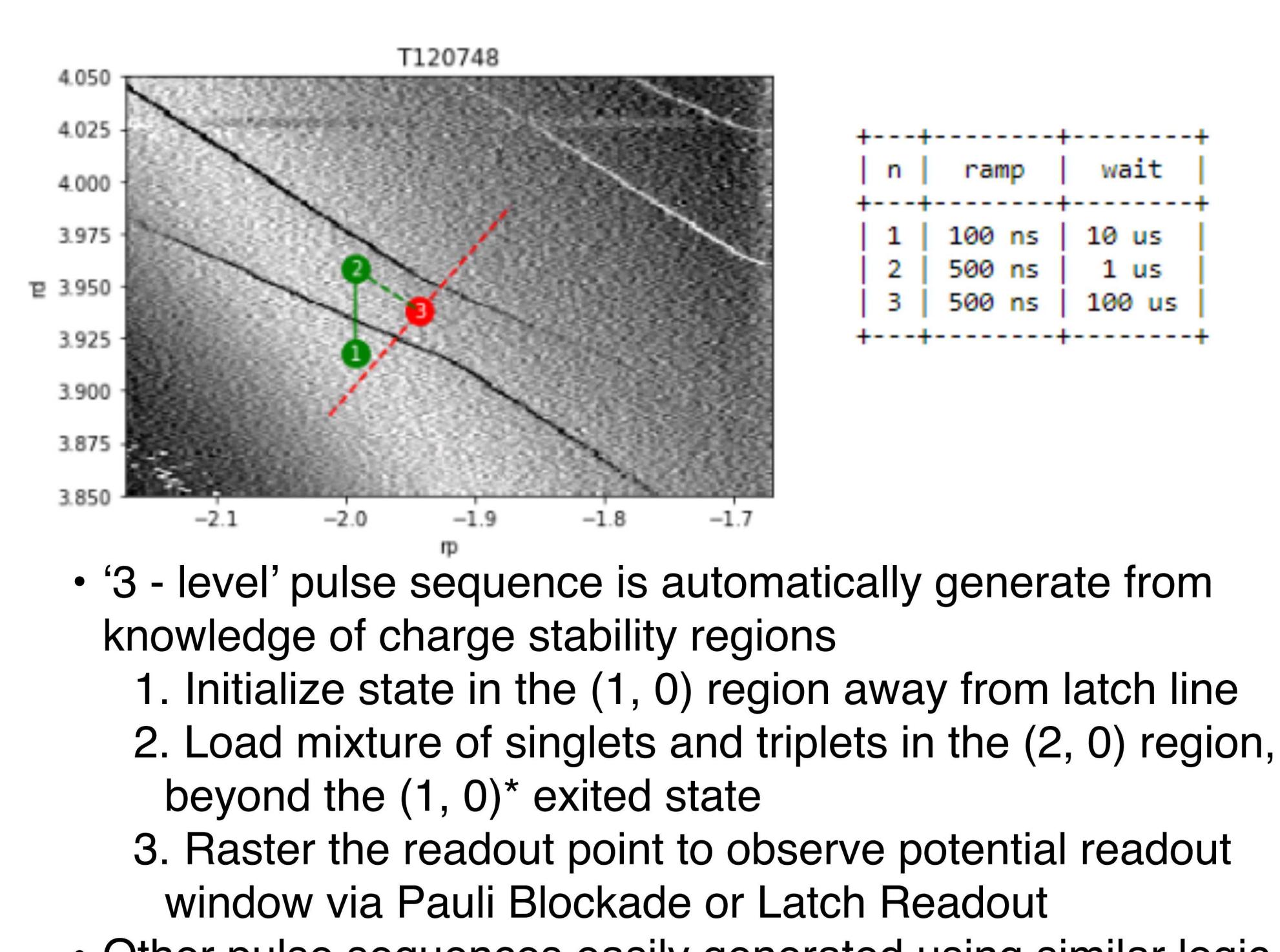
Quantify Anticrossing Parameters



Auto-Identify Stability Regions



Auto-Generate Pulse Sequence



Conclusions

Starting from a single anticrossing of interest (potential donor or double quantum dot qubit) we show we can:

- Analyze the stability diagram for triple point location and charge transition slopes
- Determine the charge filling for both the static and dynamic charge filling
- Automatically formulate a pulse sequence to begin calibrating our qubit

Future Steps:

- Analysis modules for different pulse sequence results
- Mult-qubit stability diagram navigation

[1] Hensgens et al., Nature 548, 70 (2017). [4] Kalantre et al, arXiv:1712.04914 (2018).
[2] Baart et al, APL 108, 213104 (2016). [5] Botzem et al. arXiv:1801.03755 (2018).
[3] Diepen, et al, arXiv:1803.10352v1 (2018). [6] Lapointe-Major, Masters Thesis (2017)